

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-59(Canceled)

60. (Currently Amended) A method for manufacturing a display device comprising the steps of:

forming a plurality of thin film transistors over a substrate;

forming an insulating film comprising a resin over the plurality of thin film transistors;

forming a passivation film over the insulating film; and

forming an electroluminescence element over the passivation film, said electroluminescence element comprising a first electrode formed on the passivation film, a light emitting layer formed on the first electrode and a second electrode formed on the light emitting layer.

wherein said first electrode is electrically connected to one of said thin film transistors through a contact hole through said passivation film and said insulating film.

61. (Canceled)

62. (Previously presented) A method according to claim 60 wherein the passivation film comprises an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus), or an insulating film that comprises



Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), (La) lanthanum, Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

63. (Previously presented) A method according to claim 60 wherein said passivation film comprises a material selected from the group consisting of silicon nitride and silicon oxynitride.

64. (Previously presented) A method according to claim 60 wherein said electroluminescence material comprises an organic light emitting layer.

65. (Currently Amended) A method for manufacturing a display device comprising the steps of:

forming a plurality of thin film transistors over a substrate;

forming an insulating film comprising a resin over the plurality of thin film transistors;

forming a first passivation film over the insulating film;

forming an electroluminescence element over the first passivation film, said electroluminescence element comprising an anode, a cathode and a light emitting layer interposed therebetween; and

forming a second passivation film over the electroluminescence element,

wherein the electroluminescence element is interposed between the first passivation film and the second passivation film.

66. (Canceled)



67. (Previously presented) A method according to claim 65 wherein each of the first passivation film and the second passivation film comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus).

68. (Previously presented) A method according to claim 65 wherein each of the first passivation film and the second passivation film comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), (La) lanthanum, Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

69. (Previously presented) A method according to claim 65 further comprising a step of forming an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus), between the substrate and the plurality of thin film transistors.

70. (Previously presented) A method according to claim 65 further comprising a step of forming an insulating film that comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), (La) lanthanum, Gd (gadolinium), Dy (dysprosium) and Nd (neodymium), between the substrate and the plurality of thin film transistors.



71. (Currently Amended) A method for manufacturing a display device comprising the steps of:

forming a plurality of thin film transistors over a substrate;

forming a leveling film comprising a resin over the plurality of thin film transistors;

forming a passivation film over the leveling film; and

forming an electroluminescence element over the passivation film, said electroluminescence element comprising an anode, a cathode and a light emitting layer interposed therebetween.

72. (Previously presented) A method according to claim 71 wherein the leveling film comprises a resin.

73. (Previously presented) A method according to claim 71 wherein said passivation film comprises a material selected from the group consisting of silicon nitride and silicon oxynitride.

74. (Previously presented) A method according to claim 71 wherein said electroluminescence material comprises an organic light emitting layer.

75. (Currently Amended) A method of manufacturing a display device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising silicon and nitrogen over the thin film transistor;



forming a leveling film comprising a resin over the first insulating film;

forming a second insulating film comprising silicon nitride;

forming a light emitting element over the second insulating film, said light emitting element comprising an electroluminescence layer comprising an anode, a cathode and an organic material interposed therebetween; and

forming a third insulating film comprising a material selected from the group consisting of aluminum nitride, silicon carbide, silicon nitride, boron nitride, boron phosphate and aluminum oxide.

76. (Currently Amended) A device comprising:

a substrate;

a thin film transistor formed over the substrate, said thin film transistor comprising at least a semiconductor film and a gate electrode adjacent to the semiconductor film with a gate insulating film therebetween;

a first insulating film comprising silicon, nitrogen and oxygen formed over at least the ~~crystalline~~ semiconductor film and the gate electrode;

a leveling film comprising a resin formed over the first insulating film;

a second insulating film comprising silicon nitride formed on the leveling film;

a light emitting element formed on the second insulating film, said light emitting element comprising a first electrode formed on the second insulating film, an electroluminescence layer comprising an organic material adjacent to the first electrode and a second electrode formed over the electroluminescence layer; and



a third insulating film formed over the second electrode, said third insulating film comprising a material selected from the group consisting of aluminum nitride, silicon carbide, silicon nitride, boron nitride, boron phosphate and aluminum oxide.